

Features:

- Ideal for DC – 4 GHz High Linearity / High Dynamic Range Applications
- Excellent RF Performance:
 - 45 dBm IP3
 - 70 dBc ACPR
 - 28 dBm P1dB
 - 14 dB SSG @ 2000 MHz
- MTTF > 100 years @ channel temperature 150°C
- Lead Free RoHS Compliant Surface-Mount SOT-89 Package



Description:

The MwT-1789HL is a high linearity GaAs MESFET device in low cost SOT89 package that is ideally suited for high linearity driver and Power Amplifier applications. The applications include 2G, 2.5G, and 3G wireless infrastructure standards, such as GSM, TDMA, CDMA, Edge, cdma2000, WCDMA, TD-SCDMA, and UMTS base stations. This product is also ideal for high data rate wireless LAN infrastructure applications, such as high QAM rate 802.11 WiFi and 802.16 WiMax base stations and APs (Access Points). In addition, the product can be used for point-to-point microwave communications links. The third order intercept performance of the MwT-1789HL is excellent, typically 18 dB above the 1 dB power gain compression point. The chip is produced using MwT's proprietary high linearity device design. It also uses MwT reliable metallization process. All chips are passivated using MwT's patented "Diamond-Like Carbon" process for increased durability.

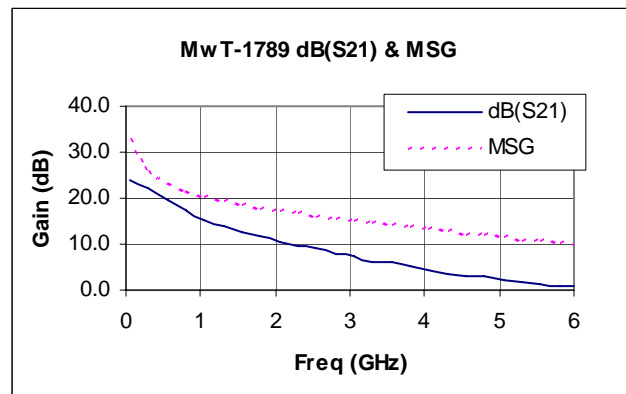
Electrical Specifications⁽¹⁾: @ $V_{ds}=6.5V$, $I_{ds}=200mA$, $T_a=25\text{ }^{\circ}C$

Parameter	Units	Typical Data			
		900	1950	2500	3500
Test Frequency	MHz	900	1950	2500	3500
Gain	dB	18	14	11	10
Input Return Loss	dB	10	10	10	9
Output Return Loss	dB	10	8	9	9
Output P1dB	dBm	28.5	28.5	28	28
Output IP3	dBm	45	45	45	45
Noise Figure ⁽²⁾	dB	3	3	4	4

1. RF data is taken from an application circuit. See application notes for details of RF performance and configuration of application circuit.
2. Noise Figure is taken at $I_{ds}=100mA$.

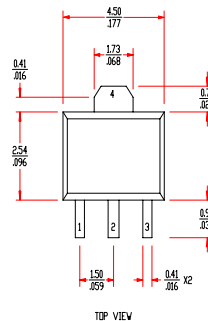
DC Specifications: ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETERS & CONDITIONS	UNITS	MIN	TYP	MAX
IDSS	Saturated Drain Current Vds=3.0 V Vgs=0.0 V	mA	440		680
Gm	Transconductance Vds=2.0 V Vgs=0.0 V	mS		380	
Vp	Pinch-off Voltage Vds=3.0 V Ids=16.0 mA	V		-2.5	-5.0
BVGSO	Gate-to-Source Breakdown Voltage Igs= -2.4 mA	V	-6.0	-12.0	
BVGDO	Gate-to-Drain Breakdown Voltage Igd= -2.4 mA	V	-9.0	-12.0	
Rth	Thermal Resistance	$^\circ\text{C}/\text{W}$		30	



SOT-89 Outline Diagram

OUTLINE DRAWING



1: Gate; 2,4: Source; 3: Drain
Dimensions in mm/inch

Typical Scattering Parameters:

(Vds=6.5V, Ids=200mA, Ta =25°C Reference Planes at Leads)

F [GHz]	S11		S21		S12		S22	
	Mag	Ang	Mag	Ang	Mag	Ang	Mag	Ang
0.250	0.883	-62.592	13.372	145.807	0.030	54.281	0.199	-61.148
0.500	0.822	-101.770	9.977	124.388	0.042	42.491	0.205	-99.716
0.750	0.788	-125.905	7.610	111.294	0.049	36.904	0.207	-120.156
1.000	0.772	-141.758	6.104	102.405	0.051	35.628	0.207	-132.755
1.250	0.765	-153.729	5.130	95.579	0.056	35.655	0.205	-141.214
1.500	0.762	-163.638	4.378	88.965	0.056	35.370	0.201	-149.045
1.750	0.762	-172.772	3.909	84.423	0.060	38.592	0.198	-156.773
2.000	0.760	178.628	3.503	77.228	0.063	35.009	0.196	-165.448
2.250	0.761	170.294	3.103	72.602	0.063	38.580	0.201	-175.051
2.500	0.765	162.141	2.867	67.380	0.067	37.582	0.210	174.935
2.750	0.768	154.540	2.561	61.985	0.067	38.516	0.224	165.112
3.000	0.772	147.101	2.384	57.569	0.068	38.547	0.238	156.386
3.250	0.779	140.309	2.140	51.937	0.069	41.708	0.257	148.369
3.500	0.781	133.919	1.966	49.164	0.072	41.931	0.276	141.018
3.750	0.781	128.561	1.859	45.298	0.072	42.125	0.295	134.092
4.000	0.782	123.650	1.687	40.539	0.075	45.268	0.313	128.716
4.250	0.788	119.391	1.576	38.185	0.072	45.630	0.332	125.490
4.500	0.792	114.854	1.477	35.447	0.080	51.701	0.358	122.346
4.750	0.796	110.082	1.413	30.992	0.086	49.126	0.378	118.908
5.000	0.795	105.529	1.291	28.392	0.088	51.114	0.394	114.941
5.250	0.792	100.361	1.271	24.881	0.096	49.424	0.403	110.320
5.500	0.796	95.934	1.170	19.496	0.096	45.481	0.410	104.083
5.750	0.799	90.277	1.125	18.186	0.105	48.822	0.426	98.804
6.000	0.804	84.180	1.088	13.075	0.112	46.367	0.446	91.560

Absolute Maximum Ratings: (Ta= 25 °C)*

SYMBOL	PARAMETERS	UNITS	ABSOLUTE MAXIMUM
Vds	Drain-Source Voltage	V	8
Vgs	Gate-Source Voltage	V	-6 to +0.8
Ids	Drain Current	mA	400
Igs	Gate Current	mA	3
Pdiss	DC Power Dissipation	W	2.5
Pin max	RF Input Power	dBm	+28
Tch	Channel Temperature	°C	150
Tstg	Storage Temperature	°C	-60 to 150

*Operation of this device above any one of these parameters may cause permanent damage.